


[简体中文](#) | [繁體中文](#) | [한국어](#) | [日本語](#)
Text Size [A](#) [A](#)

Site Search

Search

[Site Map](#)

HOME, Products > Discrete Semiconductors > Transistors > Complex Transistors > SP8M51

ICs

Discrete Semiconductors

Transistors

MOSFETs

Bipolar Transistors

Digital Transistors

Complex Transistors

Diodes

Opto Electronics

Passive Components

Modules (Sub Systems)

Energy Saving!
ECO Devices
 Product Information →

4V Drive Nch+Pch MOSFET

SP8M51 **NEW**[Inquiries concerning our products](#)

Data Sheet

Design Model

[Reliability information](#)[Operation notes](#)[Condition of soldering](#)[Print out](#)

[Product description]

Complex type MOSFETs(P+N) are made as low ON-resistance devices by the micro-processing technologies useful for wide range of applications. Broad lineup covering compact types, high-power types and complex types to meet various needs in the market.

Features

- 4V-drive type Nch+Pch Middle-power MOSFET

Product specifications

Absolute maximum ratings (Ta=25°C)		
Rated parameters	Standard value	Conditions
Drain-Source voltage $V_{DS}(V)$	100	
Gate-Source voltage $V_{GS}(V)$	±20	
Drain current(continuous) $I_D(A)$	±3	
Source current(body Di) $I_S(A)$	1	
Total power dissipation $P_D(W)$	2	Mounted on a ceramic board
Channel temperature $T_{ch}(°C)$	150	
Storage temperature $T_{stg}(°C)$	-55 to +150	

Absolute maximum ratings (Ta=25°C)		
Rated parameters	Standard value	Conditions
Drain-Source voltage $V_{DS}(V)$	-100	
Gate-Source voltage $V_{GS}(V)$	±20	
Drain current(continuous) $I_D(A)$	±2.5	
Source current(body Di) $I_S(A)$	-1	
Total power dissipation $P_D(W)$	2	Mounted on a ceramic board
Channel temperature $T_{ch}(°C)$	150	
Storage temperature $T_{stg}(°C)$	-55 to +150	

*The contents described here are just outline for introduction.

Please obtain the specification sheets from us for thorough check before use.

Status Product

Part No.	Package	Status *1	RoHS	Packing style	Package quantity	Samples *2	Sales
SP8M51TB	SOP8	Active	Yes	Taping	2500		Inquiry

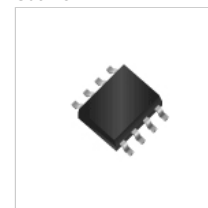
*1 Active: Production or current type Preparation: Preliminary type Preview: Development type

*2 Display ranks are representative hFE rank. Please understand that selection of hFE rank is not possible.

Others

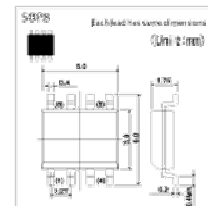
Please check the details on "[Product List](#)" for Others.

Outline



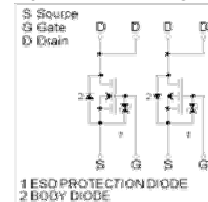
SOP8

Dimensions



* Click to enlarge.

Equivalent circuit diagram



Transistors

2010.07.21

The industry's highest efficiency MOSFETs for DC/DC power supplies: ECOMOS™

2010.02.25

ROHM's ultra-low voltage drive MOSFETs - ECOMOS™ - enable driving from a control voltage of 0.9V

2010.01.22

ROHM continues to offer its lineup of ultra-low voltage MOSFETs ECOMOS™ series

2009.05.29

High speed trr High Voltage Resistance PrestoMOS™ Series

2009.02.27

ROHM's new RC series of 250V MOSFETs

[Precautions for driving TRs safety](#)
[Knowledge required for the die temp. calculation](#)
[What is a transistor?](#)
[Operation notes](#)[Part No. explanation](#)[Package](#)[Taping specifications](#)
[Soldering conditions](#)
 >Surface mounted type transistors
 >Leaded type transistors
[Storage conditions](#)[Explanation of symbols](#)[FAQ](#)
[ROHM Internet Direct Shopping](#)
[RoHS directive compliance](#)[Contact us](#)